30 V, single P-channel Trench MOSFET 10 September 2012

Product data sheet

1. Product profile

1.1 General description

P-channel enhancement mode Field-Effect Transistor (FET) in a leadless medium power DFN2020MD-6 (SOT1220) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

1.2 Features and benefits

- Trench MOSFET technology
- Small and leadless ultra thin SMD plastic package: 2 x 2 x 0.65 mm
- Exposed drain pad for excellent thermal conduction
- Tin-plated 100 % solderable side pads for optical solder inspection

1.3 Applications

- Charging switch for portable devices
- DC-to-DC converters
- Power management in battery-driven portable devices
- Hard disk and computing power management

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j = 25 °C		-	-	-30	V
V_{GS}	gate-source voltage			-20	_	20	V
I _D	drain current	V _{GS} = -10 V; T _{amb} = 25 °C; t ≤ 5 s	[1]	-	-	-6.8	Α
Static characteristics							
R _{DSon}	drain-source on-state resistance	V_{GS} = -10 V; I_D = -4.7 A; T_j = 25 °C		-	40	50	mΩ

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².



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2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	D	drain	1 6	D
2	D	drain	7 7	
3	G	gate		G T T
4	S	source	3 8 4	\$ 017aaa257
5	D	drain	Transparent top view	
6	D	drain	DFN2020MD-6 (SOT1220)	
7	D	drain		
8	S	source		

3. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PMPB48EP	DFN2020MD-6	plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals	SOT1220			

4. Marking

Table 4. Marking codes

Type number	Marking code
PMPB48EP	1U

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-30	V
V _{GS}	gate-source voltage			-20	20	V
I _D	drain current	V _{GS} = -10 V; T _{amb} = 25 °C; t ≤ 5 s	[1]	-	-6.8	Α
		V _{GS} = -10 V; T _{amb} = 25 °C	[1]	-	-4.7	Α
		V _{GS} = -10 V; T _{amb} = 100 °C	[1]	-	-3	Α
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \mu s$		-	-19	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C	[1]	-	1.7	W
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Symbol	Parameter	Conditions		Min	Max	Unit
		T _{amb} = 25 °C; t ≤ 5 s	[1]	-	3.5	W
		T _{sp} = 25 °C		-	12.5	W
Tj	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drai	in diode					
I _S	source current	T _{amb} = 25 °C	[1]	-	-1.8	Α

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².

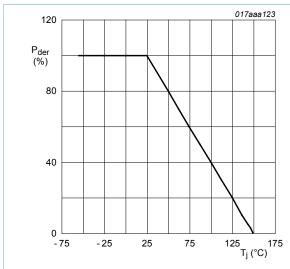


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

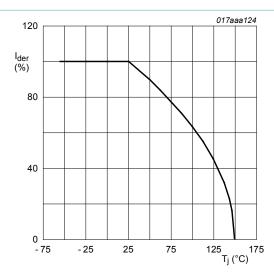


Fig. 2. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}\text{C})}} \times 100 \%$$

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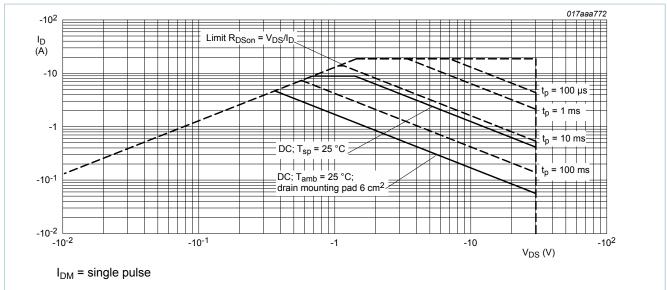


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)} thermal resistar from junction to ambient	thermal resistance		[1]	-	235	270	K/W
	_		[2]	-	67	74	K/W
	ambient	in free air; t ≤ 5 s	[2]	-	33	36	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	5	10	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².

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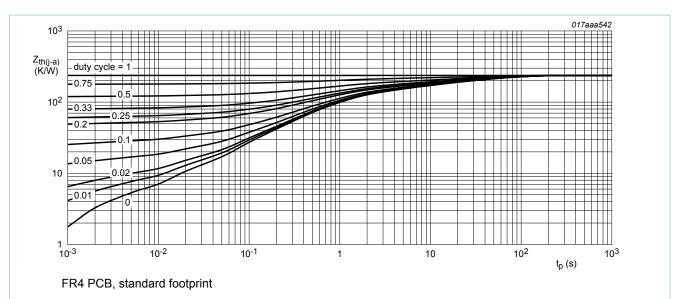


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

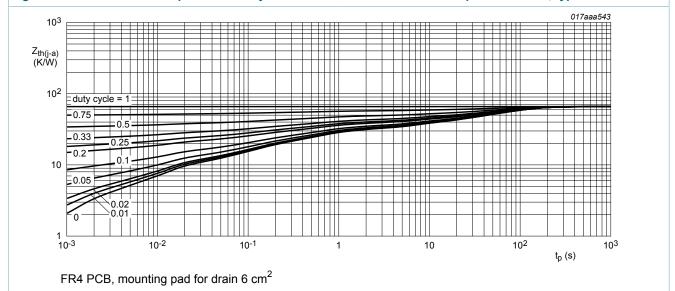


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

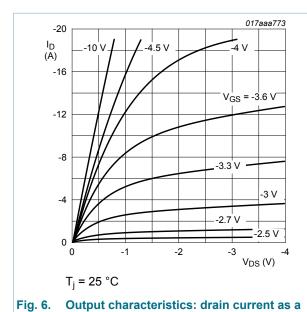
7. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
Static chara	Static characteristics							
V _{(BR)DSS}	drain-source breakdown voltage	$I_D = -250 \mu A; V_{GS} = 0 V; T_j = 25 °C$		-30	-	-	V	
V_{GSth}	gate-source threshold voltage	$I_D = -250 \mu A; V_{DS} = V_{GS}; T_j = 25 °C$		-1	-1.5	-2.5	V	
I _{DSS}	drain leakage current	$V_{DS} = -30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$		-	-	-1	μΑ	
I _{GSS}	gate leakage current	V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C		-	-	-100	nA	
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drain-source on-state resistance	$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$ $V_{GS} = -10 \text{ V}; I_D = -4.7 \text{ A}; T_j = 25 \text{ °C}$		-	_	400	^
	\/ - 10\/:			_	100	nA
resistance	V _{GS} = -10 V, I _D = -4.7 A, I _j = 25 C		-	40	50	mΩ
	V_{GS} = -10 V; I_D = -4.7 A; T_j = 150 °C		-	60	75	mΩ
	V_{GS} = -4.5 V; I_D = -3.9 A; T_j = 25 °C		-	55	76	mΩ
forward transconductance	V_{DS} = -10 V; I_D = -4.7 A; T_j = 25 °C		-	15	-	S
gate resistance	f = 1 MHz		-	6	-	Ω
cteristics						_
total gate charge	V_{DS} = -15 V; I_{D} = -4.7 A; V_{GS} = -10 V;		-	17	26	nC
gate-source charge	T _j = 25 °C		-	2.5	-	nC
gate-drain charge			-	3.2	-	nC
input capacitance	V_{DS} = -15 V; f = 1 MHz; V_{GS} = 0 V; T_j = 25 °C		-	860	-	pF
output capacitance			-	105	-	pF
reverse transfer capacitance			-	87	-	pF
turn-on delay time	V_{DS} = -15 V; I_{D} = -4.7 A; V_{GS} = -10 V;		-	7.4	-	ns
rise time	$R_{G(ext)} = 6 \Omega$; $T_j = 25 °C$		-	17.5	-	ns
turn-off delay time			-	27	-	ns
fall time			-	10.4	-	ns
iode						
source-drain voltage	I_S = -1.8 A; V_{GS} = 0 V; T_j = 25 °C		-	-0.8	-1.2	V
	transconductance gate resistance cteristics total gate charge gate-source charge gate-drain charge input capacitance output capacitance reverse transfer capacitance turn-on delay time rise time turn-off delay time fall time ode	$V_{GS} = -4.5 \text{ V; } I_D = -3.9 \text{ A; } T_j = 25 \text{ °C}$ forward transconductance	$V_{GS} = -4.5 \text{ V; } I_D = -3.9 \text{ A; } T_j = 25 \text{ °C}$ forward transconductance $V_{DS} = -10 \text{ V; } I_D = -4.7 \text{ A; } T_j = 25 \text{ °C}$ total gate resistance $f = 1 \text{ MHz}$ $Cteristics$ total gate charge $V_{DS} = -15 \text{ V; } I_D = -4.7 \text{ A; } V_{GS} = -10 \text{ V; } I_D = 25 \text{ °C}$ gate-source charge $V_{DS} = -15 \text{ V; } I_D = -4.7 \text{ A; } V_{GS} = -10 \text{ V; } I_D = 25 \text{ °C}$ gate-drain charge $V_{DS} = -15 \text{ V; } I_D = -4.7 \text{ A; } V_{GS} = 0 \text{ V; } I_D = 25 \text{ °C}$ output capacitance $V_{DS} = -15 \text{ V; } I_D = -4.7 \text{ A; } V_{GS} = -10 \text{ V; } I$	$V_{GS} = -4.5 \text{ V; } I_D = -3.9 \text{ A; } T_j = 25 \text{ °C}$ - forward transconductance gate resistance	$V_{GS} = -4.5 \text{ V; } I_D = -3.9 \text{ A; } T_j = 25 \text{ °C} \qquad - 55$ forward transconductance $V_{DS} = -10 \text{ V; } I_D = -4.7 \text{ A; } T_j = 25 \text{ °C} \qquad - 15$ forward transconductance $V_{DS} = -10 \text{ V; } I_D = -4.7 \text{ A; } T_j = 25 \text{ °C} \qquad - 6$ $\frac{15}{15}$ total gate resistance $V_{DS} = -15 \text{ V; } I_D = -4.7 \text{ A; } V_{GS} = -10 \text{ V; } - 17$ gate-source charge $V_{DS} = -15 \text{ V; } I_D = -4.7 \text{ A; } V_{GS} = -10 \text{ V; } - 2.5$ gate-drain charge $V_{DS} = -15 \text{ V; } f = 1 \text{ MHz; } V_{GS} = 0 \text{ V; } - 860$ output capacitance $V_{DS} = -15 \text{ V; } f = 1 \text{ MHz; } V_{GS} = 0 \text{ V; } - 860$ output capacitance $V_{DS} = -15 \text{ V; } I_D = -4.7 \text{ A; } V_{GS} = -10 \text{ V; } - 7.4$ rise time $V_{DS} = -15 \text{ V; } I_D = -4.7 \text{ A; } V_{GS} = -10 \text{ V; } - 7.4$ rise time $V_{DS} = -15 \text{ V; } I_D = -4.7 \text{ A; } V_{GS} = -10 \text{ V; } - 7.4$ fall time $V_{DS} = -15 \text{ V; } I_D = -4.7 \text{ A; } V_{GS} = -10 \text{ V; } - 7.4$ fall time $V_{DS} = -15 \text{ V; } I_D = -4.7 \text{ A; } V_{GS} = -10 \text{ V; } - 7.4$ fall time $V_{DS} = -15 \text{ V; } I_D = -4.7 \text{ A; } V_{GS} = -10 \text{ V; } - 7.4$ fall time $V_{DS} = -15 \text{ V; } I_D = -4.7 \text{ A; } V_{GS} = -10 \text{ V; } - 7.4$ fall time $V_{DS} = -15 \text{ V; } I_D = -4.7 \text{ A; } V_{GS} = -10 \text{ V; } - 7.4$ fall time $V_{DS} = -15 \text{ V; } I_D = -4.7 \text{ A; } V_{GS} = -10 \text{ V; } - 7.4$ fall time $V_{DS} = -15 \text{ V; } I_D = -4.7 \text{ A; } V_{GS} = -10 \text{ V; } - 7.4$ fall time $V_{DS} = -15 \text{ V; } I_D = -4.7 \text{ A; } V_{GS} = -10 \text{ V; } - 7.4$ fall time $V_{DS} = -15 \text{ V; } I_D = -4.7 \text{ A; } V_{GS} = -10 \text{ V; } - 7.4$ fall time $V_{DS} = -15 \text{ V; } I_D = -4.7 \text{ A; } V_{GS} = -10 \text{ V; } - 7.4$ fall time $V_{DS} = -15 \text{ V; } I_D = -4.7 \text{ A; } V_{GS} = -10 \text{ V; } - 7.4$ fall time $V_{DS} = -15 \text{ V; } I_D = -4.7 \text{ A; } V_{GS} = -10 \text{ V; } - 7.4$ fall time $V_{DS} = -15 \text{ V; } I_D = -4.7 \text{ A; } V_{GS} = -10 \text{ V; } - 7.4$ fall time $V_{DS} = -15 \text{ V; } I_D = -4.7 \text{ A; } V_{GS} = -10 \text{ V; } - 7.4$ fall time $V_{DS} = -15 \text{ V; } I_D = -4.7 \text{ A; } V_{GS} = -10 \text{ V; } - 7.4$ fall time $V_{$	$V_{GS} = -4.5 \text{ V; } I_D = -3.9 \text{ A; } T_j = 25 \text{ °C} \qquad - 55 \qquad 76$ forward transconductance $V_{DS} = -10 \text{ V; } I_D = -4.7 \text{ A; } T_j = 25 \text{ °C} \qquad - 15 \qquad $



function of drain-source voltage; typical values

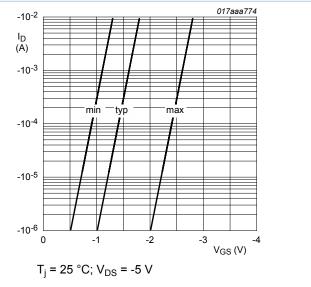


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

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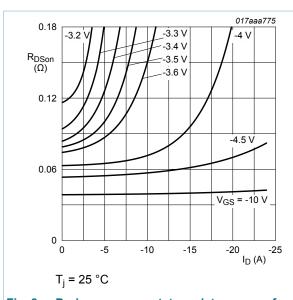


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

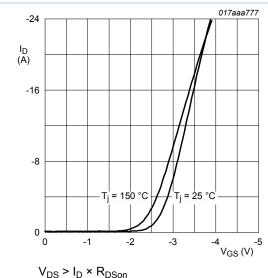


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

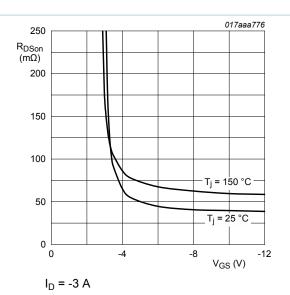


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

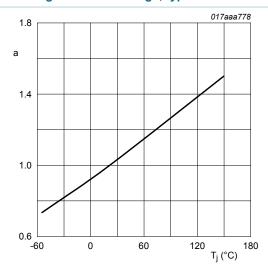


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

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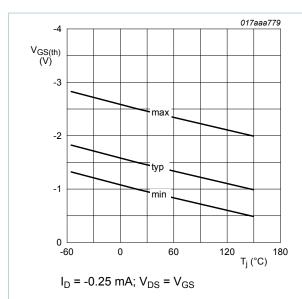


Fig. 12. Gate-source threshold voltage as a function of junction temperature

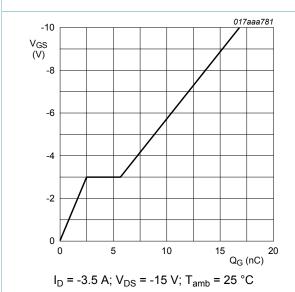


Fig. 14. Gate-source voltage as a function of gate charge; typical values

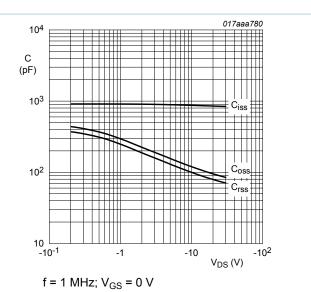


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

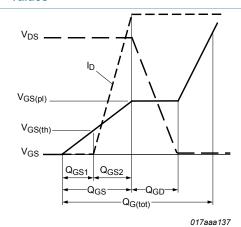
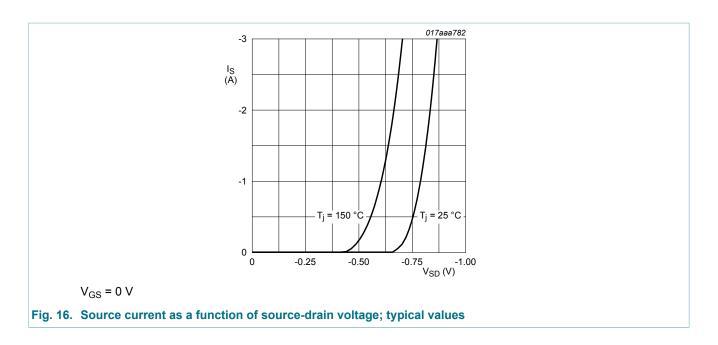
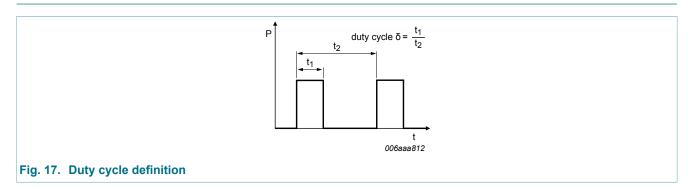


Fig. 15. Gate charge waveform definitions

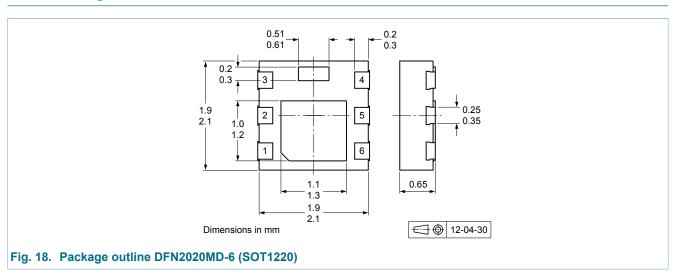
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8. Test information



9. Package outline

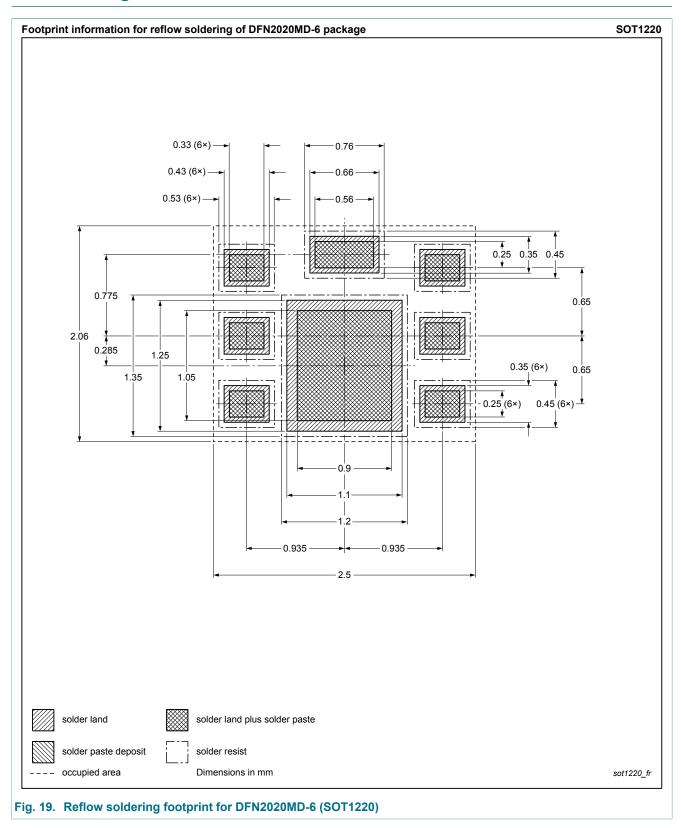


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10. Soldering



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11. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMPB48EP v.1	20120910	Product data sheet	-	-

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12. Legal information

12.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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